

Silicon NPN Power Transistors

2SD1677

DESCRIPTION

- With TO-3PN package
- High breakdown voltage
- High reliability
- Fast speed

APPLICATIONS

- For TV horizontal output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

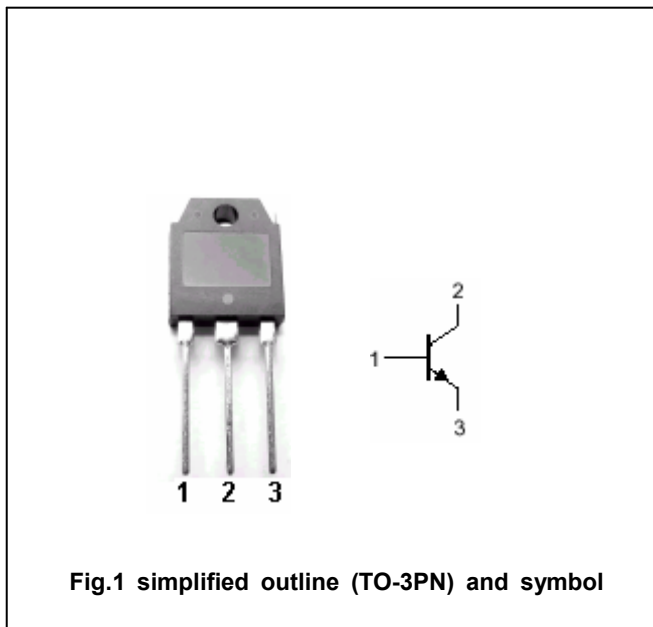


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	1500	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	800	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	6	V
I <sub>C</sub>	Collector current		5	A
P <sub>C</sub>	Collector power dissipation	T <sub>a</sub> =25□	2.5	W
		T <sub>C</sub> =25□	100	
T <sub>j</sub>	Junction temperature		150	□
T <sub>stg</sub>	Storage temperature		-55~150	□

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =100mA; I <sub>B</sub> =0	800			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA; I <sub>C</sub> =0	6			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =4.5A ; I <sub>B</sub> =2A			5.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =4.5A ; I <sub>B</sub> =2A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =800V; I <sub>E</sub> =0			10	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			10	μA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =0.5A ; V <sub>CE</sub> =5V	8			

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PACKAGE OUTLINE

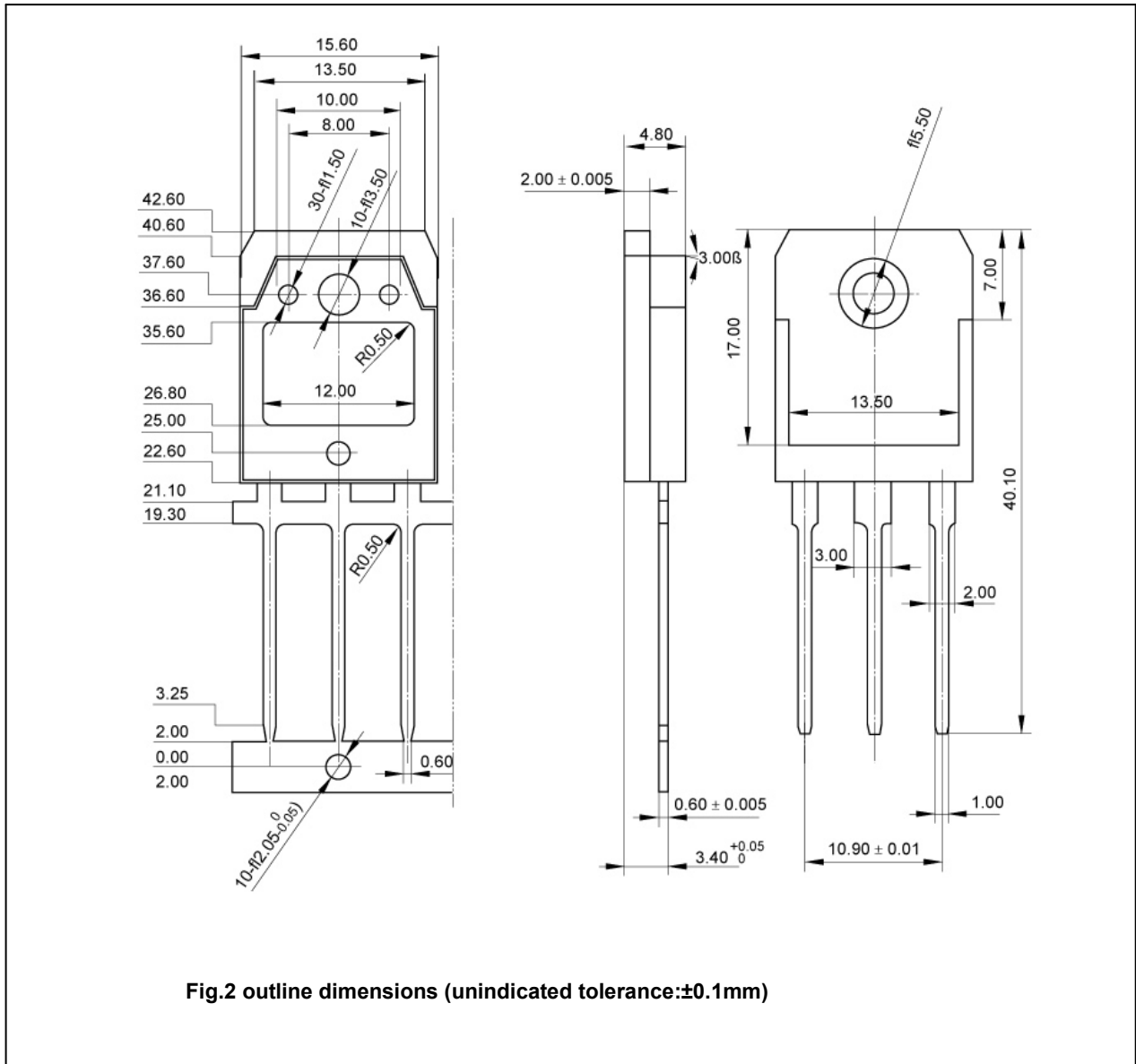


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)